

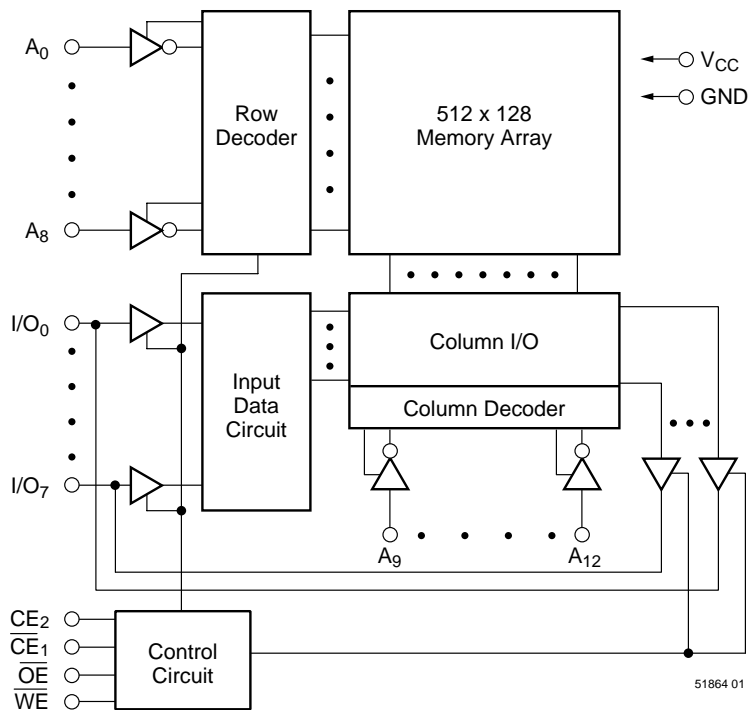
**Features**

- High-speed: 35, 70 ns
- Ultra low DC operating current of 5mA (max.)
- Low Power Dissipation:
  - TTL Standby: 2 mA (Max.)
  - CMOS Standby: 15  $\mu$ A (Max.)
- Fully static operation
- All inputs and outputs directly compatible
- Three state outputs
- Ultra low data retention current ( $V_{CC} = 2V$ )
- Single 5V  $\pm$  10% Power Supply
- Packages
  - 28-pin 600 mil PDIP
  - 28-pin 330 mil SOP (450 mil pin-to-pin)

**Description**

The V62C51864 is a 65,536-bit static random access memory organized as 8,192 words by 8 bits. It is built with MOSEL VITELIC's high performance CMOS process. Inputs and three-state outputs are TTL compatible and allow for direct interfacing with common system bus structures.

**Functional Block Diagram**



**Device Usage Chart**

Operating Temperature Range	Package Outline		Access Time (ns)		Power		Temperature Mark
	P	F	35	70	L	LL	
0°C to 70°C	•	•	•	•	•	•	Blank
-40°C to +85°C	•	•	•	•	•	•	I

**Pin Descriptions**

**A<sub>0</sub>–A<sub>12</sub> Address Inputs**

These 13 address inputs select one of the 8,192 x 8-bit words in the RAM.

**$\overline{CE}_1$ , CE<sub>2</sub> Chip Enable Inputs**

$\overline{CE}_1$  is active LOW and CE<sub>2</sub> is active HIGH. Both chip enables must be active to read from or write to the device. If either chip enable is not active, the device is deselected and is in a standby power mode. The I/O pins will be in the high-impedance state when deselected.

**$\overline{OE}$  Output Enable Input**

The Output Enable input is active LOW. When  $\overline{OE}$  is LOW with  $\overline{CE}_1$  LOW, CE<sub>2</sub> HIGH, and  $\overline{WE}$  HIGH, data of the selected memory location will be available on the I/O pins. When  $\overline{OE}$  is HIGH, the I/O pins will be in the high impedance state.

**$\overline{WE}$  Write Enable Input**

An active LOW input,  $\overline{WE}$  input controls read and write operations. When  $\overline{CE}_1$  and  $\overline{WE}$  inputs are both LOW with CE<sub>2</sub> HIGH, the data present on the I/O pins will be written into the selected memory location.

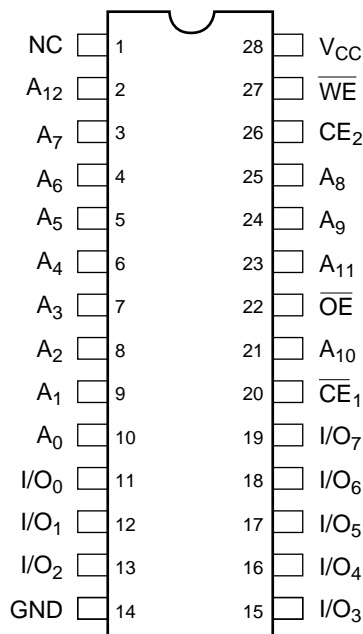
**I/O<sub>0</sub>–I/O<sub>7</sub> Data Input/Output Ports**

These 8 bidirectional ports are used to read data from and write data into the RAM.

**V<sub>CC</sub> Power Supply**

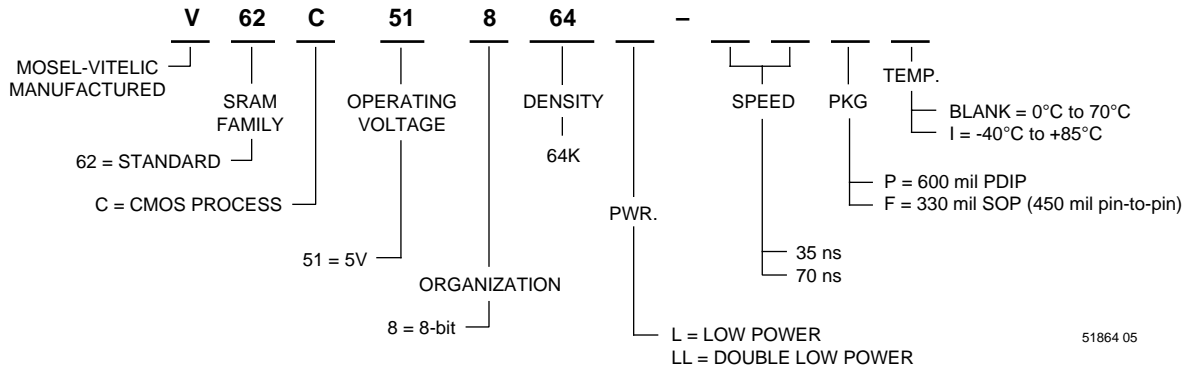
**GND Ground**

**Pin Configuration  
28-Pin Plastic DIP/SOP  
Top View**



51864 02

**Part Number Information**



**Absolute Maximum Ratings (1)**

Symbol	Parameter	Commercial	Industrial	Units
V <sub>CC</sub>	Supply Voltage	-0.5 to +7	-0.5 to +7	V
V <sub>N</sub>	Input Voltage	-0.5 to +7	-0.5 to +7	V
V <sub>DQ</sub>	Input/Output Voltage Applied	V <sub>CC</sub> + 0.5	V <sub>CC</sub> + 0.5	V
T <sub>BIAS</sub>	Temperature Under Bias	-10 to +125	-65 to +135	°C
T <sub>STG</sub>	Storage Temperature	-55 to +125	-65 to +150	°C

**NOTE:**

- Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

**Capacitance\***

T<sub>A</sub> = 25°C, f = 1.0MHz

Symbol	Parameter	Conditions	Max.	Unit
C <sub>IN</sub>	Input Capacitance	V <sub>I</sub> = 0V	6	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>O</sub> = 0V	8	pF

**NOTE:**

\* This parameter is guaranteed and not tested.

**Truth Table**

Mode	$\overline{CE}_1$	CE <sub>2</sub>	$\overline{OE}$	$\overline{WE}$	I/O Operation
Standby	H	X	X	X	High Z
Standby	X	L	X	X	High Z
Output Disable	L	H	H	H	High Z
Read	L	H	L	H	D <sub>OUT</sub>
Write	L	H	X	L	D <sub>IN</sub>

**NOTE:**

X = Don't Care, L = LOW, H = HIGH

**DC Electrical Characteristics** (over all temperature ranges,  $V_{CC} = 5V \pm 10\%$ )

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{IL}$	Input LOW Voltage <sup>(1,2)</sup>		-0.5	—	0.8	V
$V_{IH}$	Input HIGH Voltage <sup>(1)</sup>		2.2	—	6	V
$I_{IL}$	Input Leakage Current	$V_C = \text{Max}, V_{IN} = 0V \text{ to } V_{CC}$	-5	—	5	$\mu A$
$I_{OL}$	Output Leakage Current	$V_C = \text{Max}, \overline{CE} = V_{IH}, V_{OUT} = 0V \text{ to } V_{CC}$	-5	—	5	$\mu A$
$V_{OL}$	Output LOW Voltage	$V_C = \text{Min}, I_{OL} = 2.1mA$	—	—	0.4	V
$V_{OH}$	Output HIGH Voltage	$V_C = \text{Min}, I_{OH} = -1mA$	2.4	—	—	V

Symbol	Parameter	Power	Com. <sup>(4)</sup>	Ind. <sup>(4)</sup>	Units
$I_{CC}$	Operating Power Supply Current, $\overline{CE} = V_{IL}, CE_2 = V_{IH}$ , Output Open, $V_C = \text{Max.}, f = 0$	READ	5	6	mA
		WRITE	0	50	
$I_{CC1}$	Average Operating Current, $\overline{CE} = V_{IL}, CE_2 = V_{IH}$ , Output Open, $V_{CC} = \text{Max.}, f = f_{MAX}^{(3)}$		60	70	mA
$I_{SB}$	TTL Standby Current $\overline{CE}_1 \geq V_{IH}, CE_2 \leq V_{IL}, V_{CC} = \text{Max.}$	L	3	4	mA
		LL	2	3	
$I_{SB1}$	CMOS Standby Current, $\overline{CE} \geq V_{CC} - 0.2V, CE_2 \leq 0.2V, V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V, V_C = \text{Max.}$	L	60	70	$\mu A$
		LL	15	30	

**NOTES:**

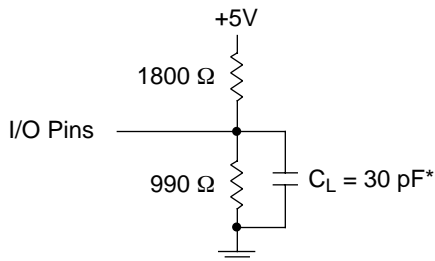
- These are absolute values with respect to device ground and all overshoots due to system or tester noise are included.
- $V_{IL}$  (Min.) = -3.0V for pulse width < 20ns.

- $f_{MAX} = 1/t_{RC}$ .
- Maximum values.

**AC Test Conditions**

Input Pulse Levels	0 to 3V
Input Rise and Fall Times	5 ns
Timing Reference Levels	1.5V
Output Load	see below

**AC Test Loads and Waveforms**



\* Includes scope and jig capacitance

**Key to Switching Waveforms**

WAVEFORM	INPUTS	OUTPUTS
	MUST BE STEADY	WILL BE STEADY
	MAY CHANGE FROM H TO L	WILL BE CHANGING FROM H TO L
	MAY CHANGE FROM L TO H	WILL BE CHANGING FROM L TO H
	DON'T CARE: ANY CHANGE PERMITTED	CHANGING: STATE UNKNOWN
	DOES NOT APPLY	CENTER LINE IS HIGH IMPEDANCE "OFF" STATE

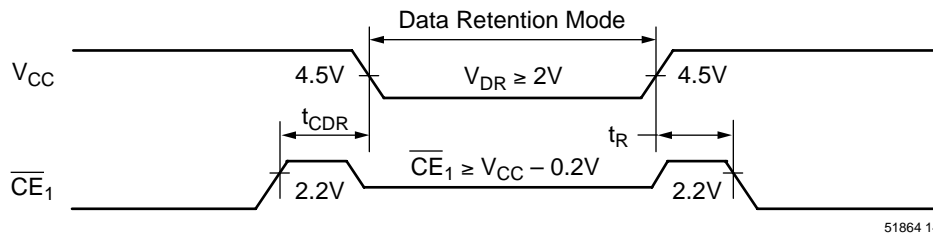
**Data Retention Characteristics**

Symbol	Parameter	Power	Min.	Typ. <sup>(2)</sup>	Max.	Units	
$V_{DR}$	$V_{CC}$ for Data Retention $\overline{CE}_1 \geq V_{CC} - 0.2V, CE_2 \leq 0.2V,$ $V_{IN} \geq V_{CC} - 0.2V, \text{ or } V_{IN} \leq 0.2V$		2.0	—	5.5	V	
$I_{CCDR}$	Data Retention Current $CE_1 \geq V_{DR} - 0.2V, CE_2 \leq 0.2V,$ $V_{IN} \geq V_{CC} - 0.2V, \text{ or } V_{IN} \leq 0.2V$	Com'l	L	—	0.5	50	$\mu A$
			LL	—	0.5	10	
		Ind.	L	—	—	70	
			LL	—	—	20	
$t_{CDR}$	Chip Deselect to Data Retention Time		0	—	—	ns	
$t_R$	Operation Recovery Time (see Retention Waveform)		$t_{RC}^{(1)}$	—	—	ns	

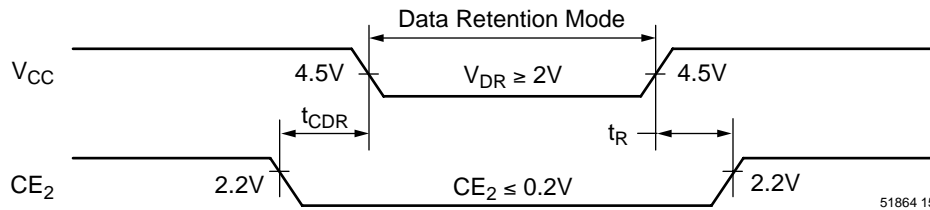
**NOTES:**

- $t_{RC}$  = Read Cycle Time
- $T_A = +25^\circ C$ .

**Low  $V_{CC}$  Data Retention Waveform (1) ( $\overline{CE}_1$  Controlled)**



**Low  $V_{CC}$  Data Retention Waveform (2) ( $CE_2$  Controlled)**



**AC Electrical Characteristics**

(over all temperature ranges)

**Read Cycle**

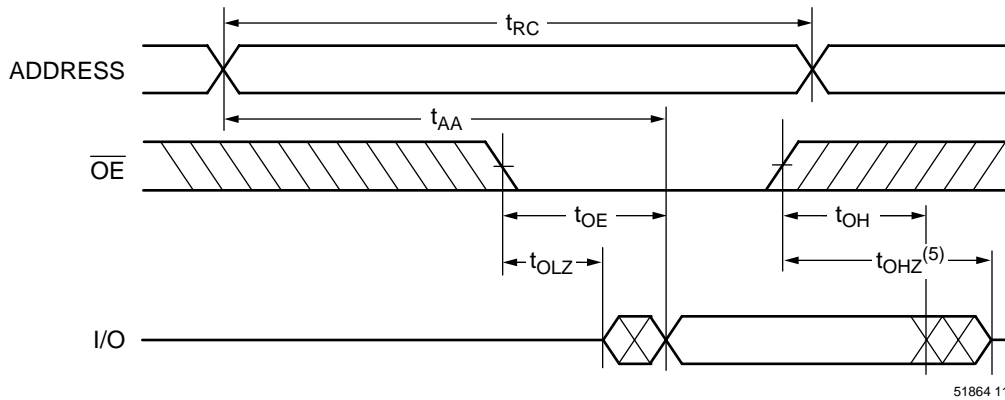
Parameter Name	Parameter	-35		-70		Unit
		Min.	Max.	Min.	Max.	
$t_{RC}$	Read Cycle Time	35	—	70	—	ns
$t_{AA}$	Address Access Time	—	35	—	70	ns
$t_{ACS1}$	Chip Enable Access Time	—	35	—	70	ns
$t_{ACS2}$	Chip Enable Access Time	—	35	—	70	ns
$t_{OE}$	Output Enable to Output Valid	—	15	—	30	ns
$t_{CLZ1}$	Chip Enable to Output in Low Z	5	—	5	—	ns
$t_{CLZ2}$	Chip Enable to Output in Low Z	5	—	5	—	ns
$t_{OLZ}$	Output Enable to Output in Low Z	5	—	5	—	ns
$t_{CHZ}$	Chip Disable to Output in High Z	0	20	0	20	ns
$t_{OHZ}$	Output Disable to Output in High Z	0	20	0	20	ns
$t_{OH}$	Output Hold from Address Change	5	—	5	—	ns

**Write Cycle**

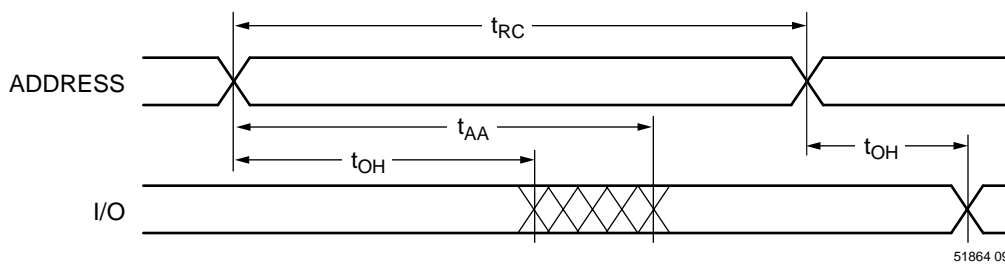
Parameter Name	Parameter	-35		-70		Unit
		Min.	Max.	Min.	Max.	
$t_{WC}$	Write Cycle Time	35	—	70	—	ns
$t_{CW}$	Chip Enable to End of Write	35	—	70	—	ns
$t_{AS}$	Address Setup Time	0	—	0	—	ns
$t_{AW}$	Address Valid to End of Write	35	—	70	—	ns
$t_{WP}$	Write Pulse Width	25	—	50	—	ns
$t_{WR}$	Write Recovery Time	0	—	0	—	ns
$t_{WHZ}$	Write to Output High-Z	0	20	0	25	ns
$t_{DW}$	Data Setup to End of Write	25	—	30	—	ns
$t_{DH}$	Data Hold from End of Write	0	—	0	—	ns
$t_{OW}$	Output Active from End of Write	5	—	5	—	ns

**Switching Waveforms (Read Cycle)**

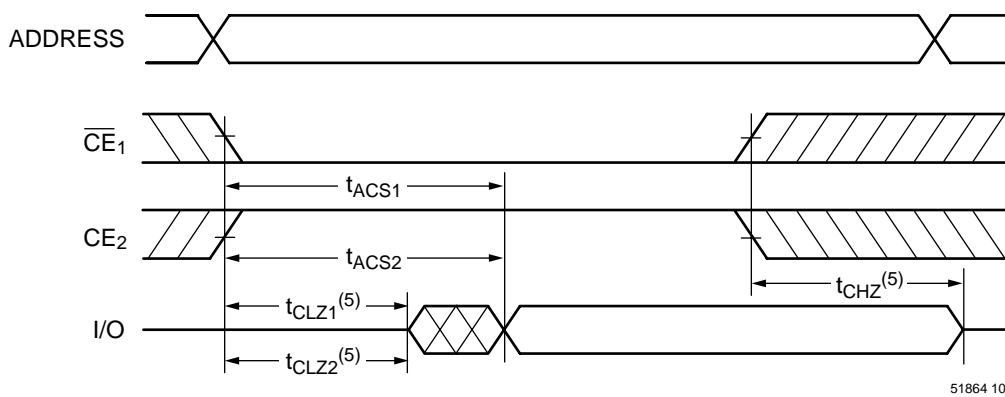
**Read Cycle 1<sup>(1, 2)</sup>**



**Read Cycle 2<sup>(1, 2, 4)</sup>**



**Read Cycle 3<sup>(1, 3, 4)</sup>**

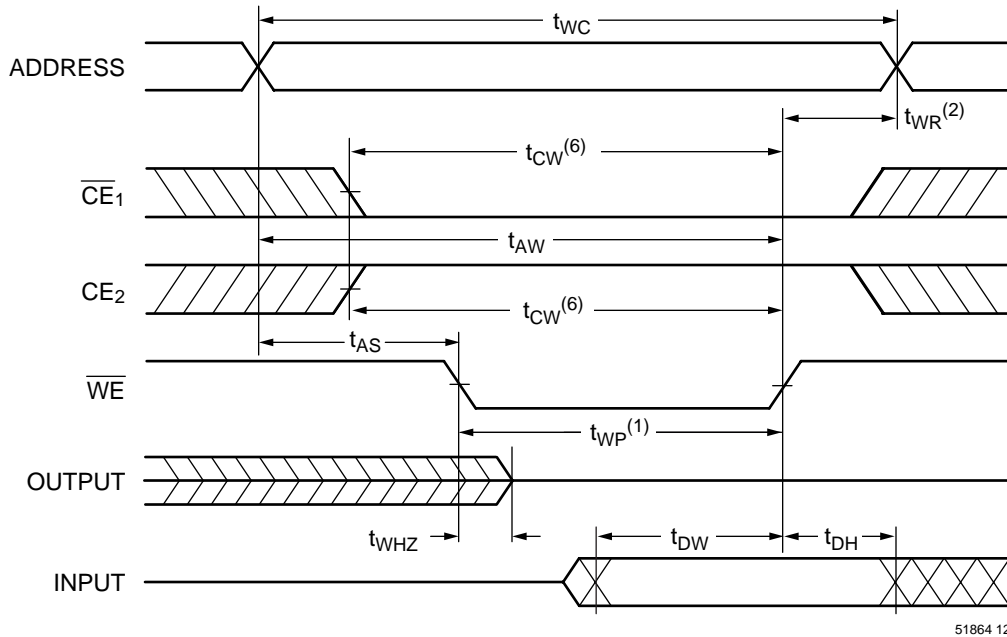


**NOTES:**

1.  $\overline{WE} = V_{IH}$ .
2.  $\overline{CE}_1 = V_{IL}$  and  $CE_2 = V_{IH}$ .
3. Address valid prior to or coincident with  $\overline{CE}_1$  transition LOW and/or  $CE_2$  transition HIGH.
4.  $\overline{OE} = V_{IL}$ .
5. Transition is measured  $\pm 500mV$  from steady state with  $C = 5pF$ . This parameter is guaranteed and not 100% tested.

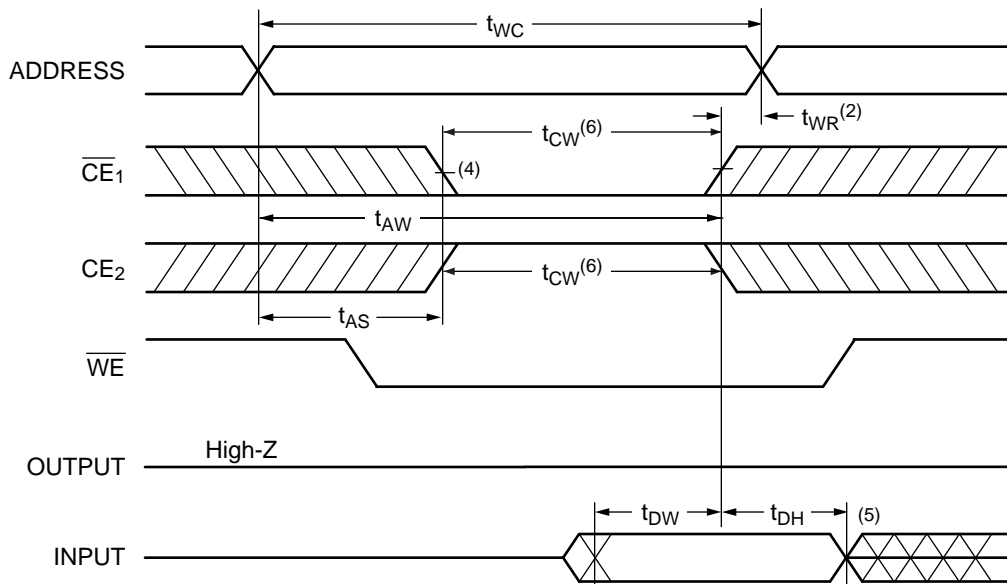
**Switching Waveforms (Write Cycle)**

**Write Cycle 1 ( $\overline{WE}$  Controlled)<sup>(4)</sup>**



51864 12

**Write Cycle 2 ( $\overline{CE}$  Controlled)<sup>(4)</sup>**



51864 13

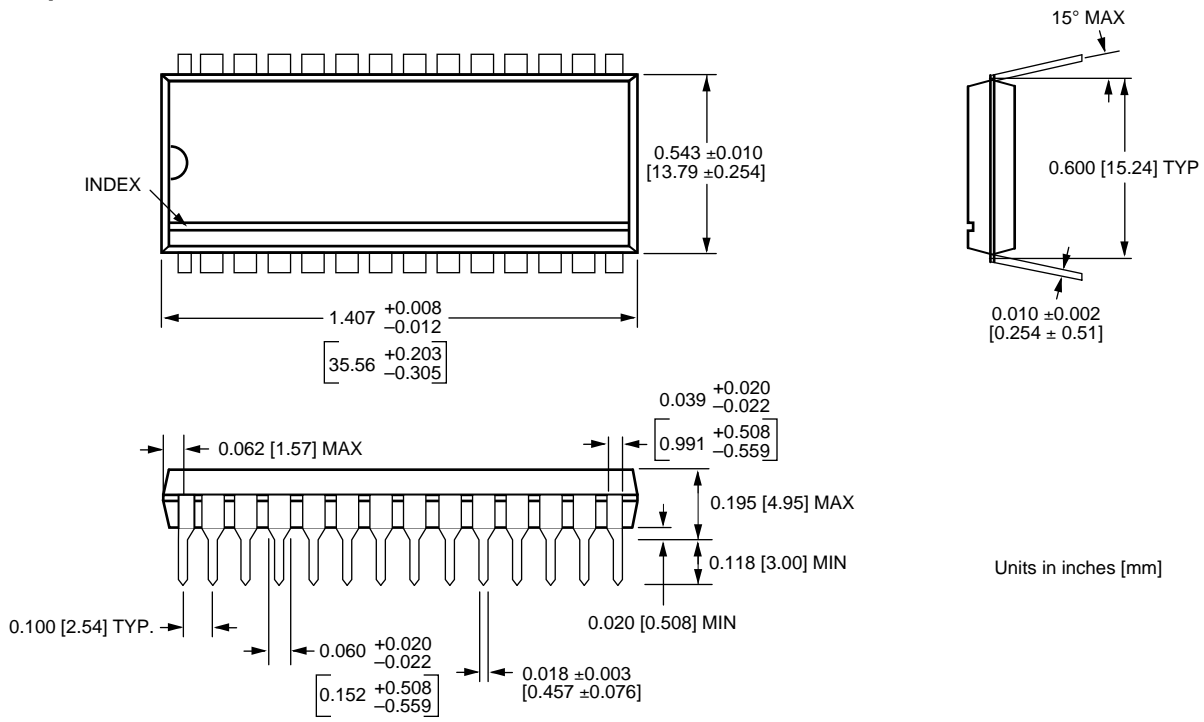
**NOTES:**

1. The internal write time of the memory is defined by the overlap of  $\overline{CE}_1$  and  $CE_2$  active and  $\overline{WE}$  low. Both signals must be active to initiate and any one signal can terminate a write by going inactive. The data input setup and hold timing should be referenced to the second transition edge of the signal that terminates the write.
2.  $t_{WR}$  is measured from the earlier of  $\overline{CE}_1$  or  $\overline{WE}$  going HIGH, or  $CE_2$  going LOW at the end of the write cycle.
3. During this period, I/O pins are in the output state so that the input signals of opposite phase to the outputs must not be applied.
4.  $\overline{OE} = V_{IL}$  or  $V_{IH}$ . However it is recommended to keep  $\overline{OE}$  at  $V_{IH}$  during write cycle to avoid bus contention.
5. If  $\overline{CE}_1$  is LOW and  $CE_2$  is HIGH during this period, I/O pins are in the output state. Then the data input signals of opposite phase to the outputs must not be applied to them.
6.  $t_{CW}$  is measured from  $\overline{CE}_1$  going LOW or  $CE_2$  going HIGH to the end of write.

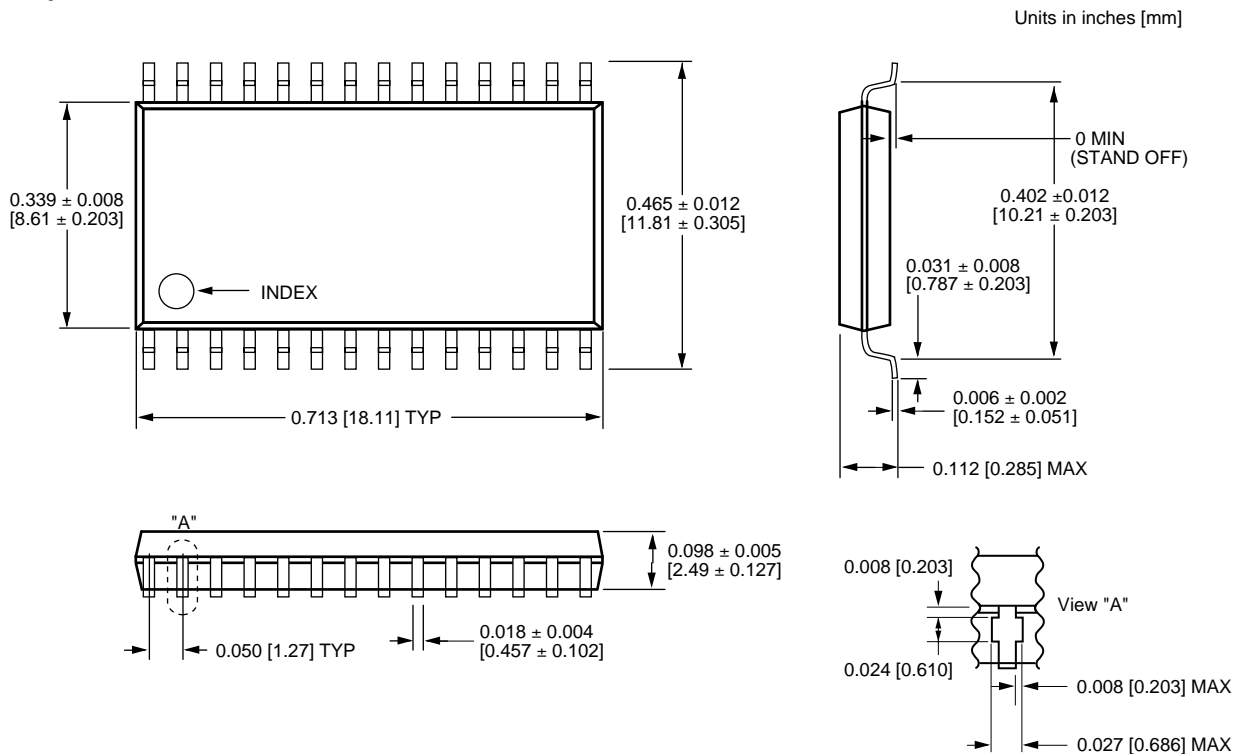


**Package Diagrams**

**28-pin 600 mil Plastic DIP**



**28-pin 330 mil SOP**



**U.S.A.**

3910 NORTH FIRST STREET  
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**HONG KONG**

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CHIBA 261-71  
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FAX: 81-43-299-6555

**IRELAND & UK**

BLOCK A UNIT 2  
BROOMFIELD BUSINESS PARK  
MALAHIDE  
CO. DUBLIN, IRELAND  
PHONE: +353 1 8038020  
FAX: +353 1 8038049

**GERMANY**

**(CONTINENTAL  
EUROPE & ISRAEL )**  
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GERMANY  
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